

## N-channel 800 V, 0.400 $\Omega$ typ., 12 A MDmesh™ K5 Power MOSFET in a D<sup>2</sup>PAK package

Datasheet - production data

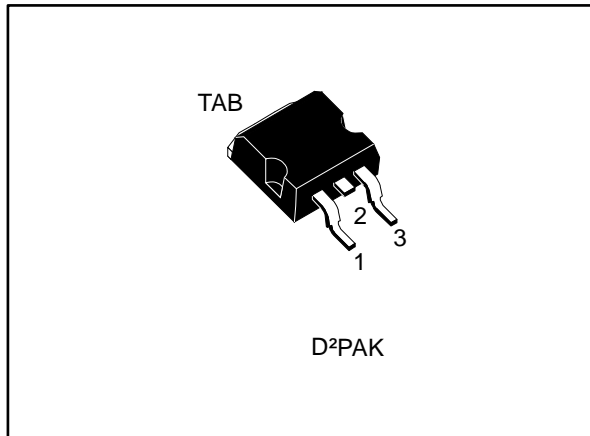
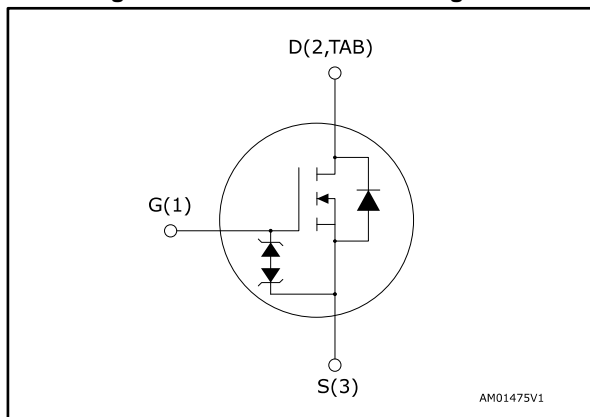


Figure 1: Internal schematic diagram



### Features

Order code	V <sub>DS</sub>	R <sub>DS(on)</sub> max.	I <sub>D</sub>
STB14N80K5	800 V	0.445 $\Omega$	12 A

- Industry's lowest R<sub>DS(on)</sub> x area
- Industry's best figure of merit (FoM)
- Ultra-low gate charge
- 100% avalanche tested
- Zener-protected

### Applications

- Switching applications

### Description

This very high voltage N-channel Power MOSFET is designed using MDmesh™ K5 technology based on an innovative proprietary vertical structure. The result is a dramatic reduction in on-resistance and ultra-low gate charge for applications requiring superior power density and high efficiency.

Table 1: Device summary

Order code	Marking	Package	Packing
STB14N80K5	14N80K5	D <sup>2</sup> PAK	Tape and reel

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# 1 Electrical ratings

**Table 2: Absolute maximum ratings**

Symbol	Parameter	Value	Unit
$V_{GS}$	Gate-source voltage	$\pm 30$	V
$I_D$	Drain current (continuous) at $T_C = 25\text{ }^\circ\text{C}$	12	A
$I_D$	Drain current (continuous) at $T_C = 100\text{ }^\circ\text{C}$	7.4	A
$I_D^{(1)}$	Drain current (pulsed)	48	A
$P_{TOT}$	Total dissipation at $T_C = 25\text{ }^\circ\text{C}$	130	W
$dv/dt^{(2)}$	Peak diode recovery voltage slope	4.5	V/ns
$dv/dt^{(3)}$	MOSFET $dv/dt$ ruggedness	50	
$T_{stg}$	Storage temperature range	- 55 to 150	$^\circ\text{C}$
$T_J$	Operating junction temperature range		

**Notes:**

<sup>(1)</sup>Pulse width limited by safe operating area.

<sup>(2)</sup> $I_{SD} \leq 12\text{ A}$ ,  $di/dt \leq 100\text{ A}/\mu\text{s}$ ;  $V_{DS(\text{peak})} < V_{(BR)DSS}$ ,  $V_{DD} = 640\text{ V}$

<sup>(3)</sup> $V_{DS} \leq 640\text{ V}$

**Table 3: Thermal data**

Symbol	Parameter	Value	Unit
$R_{thj\text{-case}}$	Thermal resistance junction-case	0.96	$^\circ\text{C}/\text{W}$
$R_{thj\text{-pcb}}^{(1)}$	Thermal resistance junction-pcb	30	$^\circ\text{C}/\text{W}$

**Notes:**

<sup>(1)</sup> When mounted on FR-4 board of 1 inch<sup>2</sup>, 2 oz Cu

**Table 4: Avalanche characteristics**

Symbol	Parameter	Value	Unit
$I_{AR}$	Avalanche current, repetitive or not repetitive (pulse width limited by $T_{j\text{max}}$ )	4	A
$E_{AS}$	Single pulse avalanche energy (starting $T_j = 25\text{ }^\circ\text{C}$ , $I_D = I_{AR}$ , $V_{DD} = 50\text{ V}$ )	270	mJ

## 2 Electrical characteristics

$T_C = 25\text{ }^\circ\text{C}$  unless otherwise specified

**Table 5: On/off-state**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$V_{GS} = 0\text{ V}$ , $I_D = 1\text{ mA}$	800			V
$I_{DSS}$	Zero gate voltage drain current	$V_{GS} = 0\text{ V}$ , $V_{DS} = 800\text{ V}$			1	$\mu\text{A}$
		$V_{GS} = 0\text{ V}$ , $V_{DS} = 800\text{ V}$ $T_C = 125\text{ }^\circ\text{C}$ <sup>(1)</sup>			50	$\mu\text{A}$
$I_{GSS}$	Gate body leakage current	$V_{DS} = 0\text{ V}$ , $V_{GS} = \pm 20\text{ V}$			$\pm 10$	$\mu\text{A}$
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$ , $I_D = 100\text{ }\mu\text{A}$	3	4	5	V
$R_{DS(on)}$	Static drain-source on-resistance	$V_{GS} = 10\text{ V}$ , $I_D = 6\text{ A}$		0.400	0.445	$\Omega$

**Notes:**

<sup>(1)</sup> Defined by design, not subject to production test.

**Table 6: Dynamic**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$C_{iss}$	Input capacitance	$V_{DS} = 100\text{ V}$ , $f = 1\text{ MHz}$ , $V_{GS} = 0\text{ V}$	-	620	-	pF
$C_{oss}$	Output capacitance		-	60	-	pF
$C_{rss}$	Reverse transfer capacitance		-	0.8	-	pF
$C_{o(tr)}$ <sup>(1)</sup>	Equivalent capacitance time related	$V_{DS} = 0\text{ to }640\text{ V}$ , $V_{GS} = 0\text{ V}$	-	107	-	pF
$C_{o(er)}$ <sup>(2)</sup>	Equivalent capacitance energy related		-	39	-	pF
$R_g$	Intrinsic gate resistance	$f = 1\text{ MHz}$ , $I_D = 0\text{ A}$	-	6.5	-	$\Omega$
$Q_g$	Total gate charge	$V_{DD} = 640\text{ V}$ , $I_D = 12\text{ A}$ $V_{GS} = 10\text{ V}$ (see <a href="#">Figure 16: "Test circuit for gate charge behavior"</a> )	-	22	-	nC
$Q_{gs}$	Gate-source charge		-	4.3	-	nC
$Q_{gd}$	Gate-drain charge		-	16.5	-	nC

**Notes:**

<sup>(1)</sup> Time related is defined as a constant equivalent capacitance giving the same charging time as  $C_{oss}$  when  $V_{DS}$  increases from 0 to 80%  $V_{DSS}$

<sup>(2)</sup> Energy related is defined as a constant equivalent capacitance giving the same stored energy as  $C_{oss}$  when  $V_{DS}$  increases from 0 to 80%  $V_{DSS}$

Table 7: Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 400\text{ V}$ , $I_D = 6\text{ A}$ , $R_G = 4.7\ \Omega$ $V_{GS} = 10\text{ V}$ see ( <i>Figure 15: "Test circuit for resistive load switching times"</i> and <i>Figure 20: "Switching time waveform"</i> )	-	12.5	-	ns
$t_r$	Rise time		-	8	-	ns
$t_{d(off)}$	Turn-off delay time		-	33	-	ns
$t_f$	Fall time		-	10	-	ns

Table 8: Source-drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$I_{SD}$	Source-drain current		-		12	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)		-		48	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 12\text{ A}$ , $V_{GS} = 0\text{ V}$	-		1.5	V
$t_{rr}$	Reverse recovery time	$I_{SD} = 12\text{ A}$ , $di/dt = 100\text{ A}/\mu\text{s}$ , $V_{DD} = 60\text{ V}$ (see <i>Figure 17: "Test circuit for inductive load switching and diode recovery times"</i> )	-	365		ns
$Q_{rr}$	Reverse recovery charge		-	4.77		$\mu\text{C}$
$I_{RRM}$	Reverse recovery current		-	26		A
$t_{rr}$	Reverse recovery time	$I_{SD} = 12\text{ A}$ , $di/dt = 100\text{ A}/\mu\text{s}$ , $V_{DD} = 60\text{ V}$ , $T_j = 150\text{ }^\circ\text{C}$ (see <i>Figure 17: "Test circuit for inductive load switching and diode recovery times"</i> )	-	485		ns
$Q_{rr}$	Reverse recovery charge		-	5.85		$\mu\text{C}$
$I_{RRM}$	Reverse recovery current		-	24		A

**Notes:**

(1) Pulse width limited by safe operating area

(2) Pulsed: pulse duration = 300  $\mu\text{s}$ , duty cycle 1.5%

Table 9: Gate-source Zener diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)GSO}$	Gate-source breakdown voltage	$I_{GS} = \pm 1\text{ mA}$ , $I_D = 0\text{ A}$	30	-	-	V

The built-in back-to-back Zener diodes are specifically designed to enhance the ESD performance of the device. The Zener voltage facilitates efficient and cost-effective device integrity protection, thus eliminating the need for additional external componentry.

## 2.2 Electrical characteristics (curves)

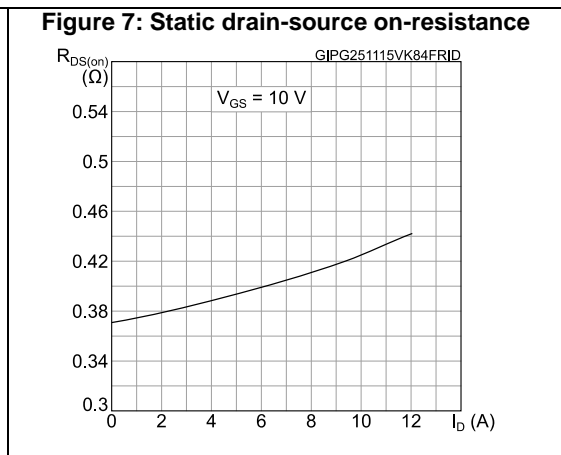
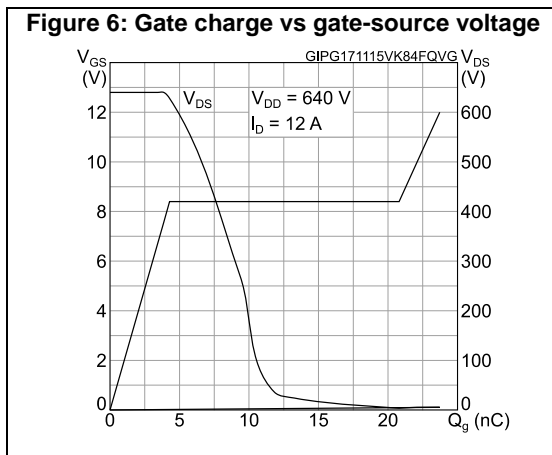
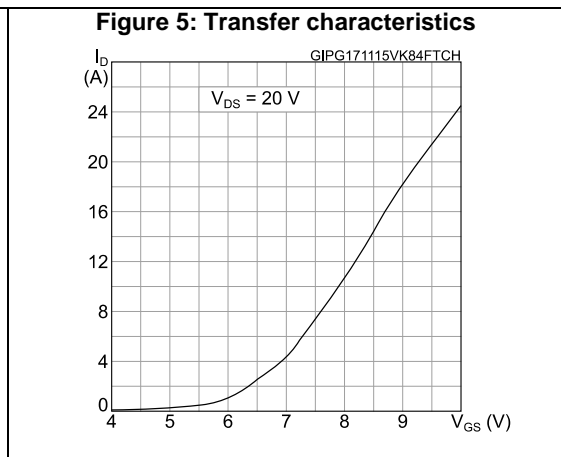
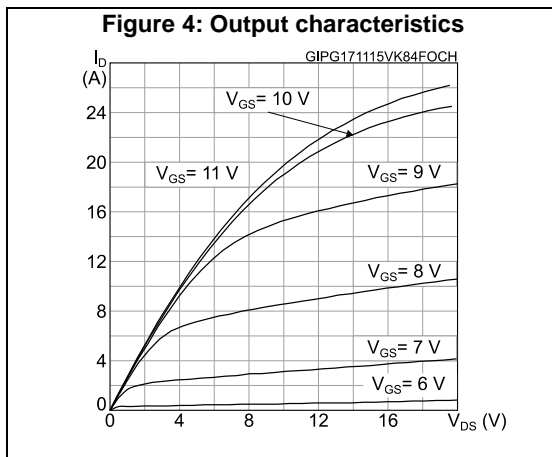
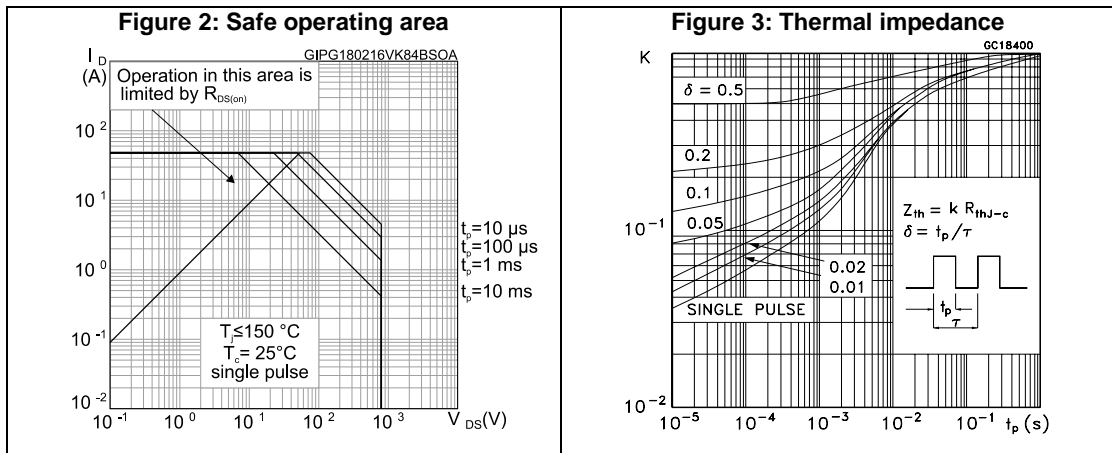


Figure 8: Capacitance variations

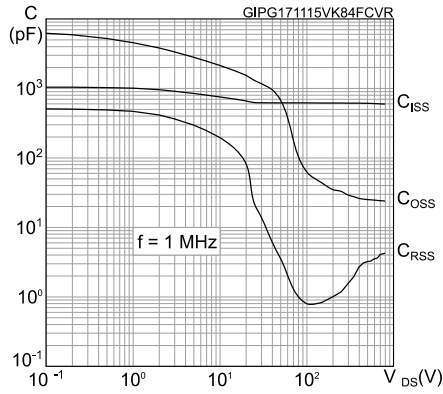


Figure 9: Normalized gate threshold voltage vs temperature

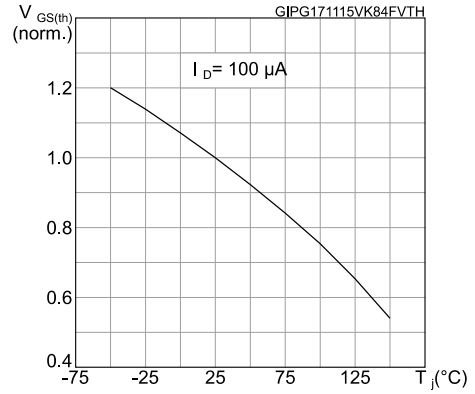


Figure 10: Normalized on-resistance vs temperature

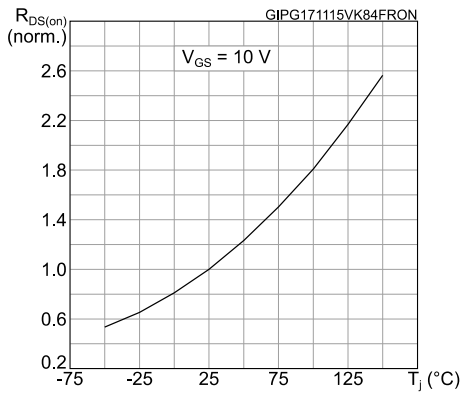


Figure 11: Normalized  $V_{(BR)DSS}$  vs temperature

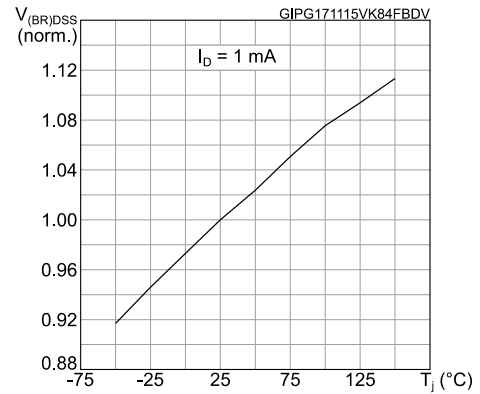


Figure 12: Maximum avalanche energy vs starting  $T_J$

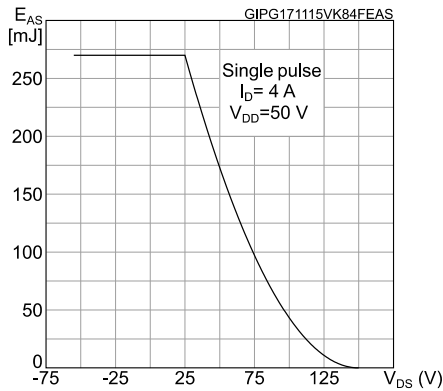


Figure 13: Source-drain diode forward characteristics

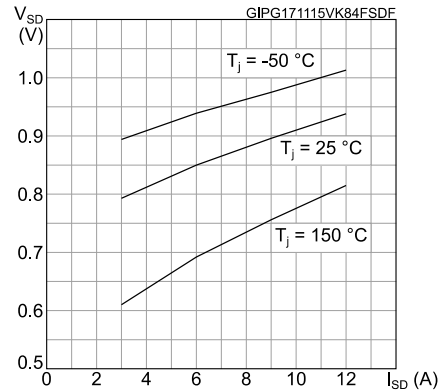
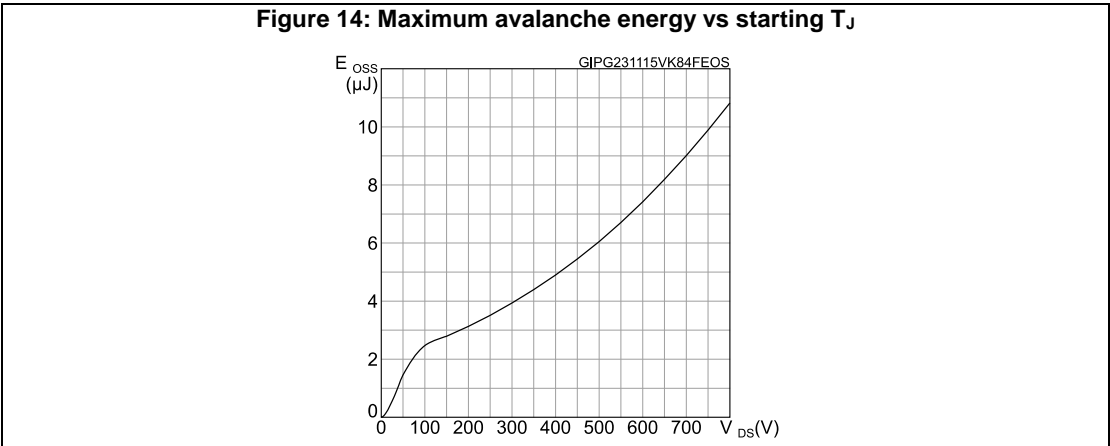


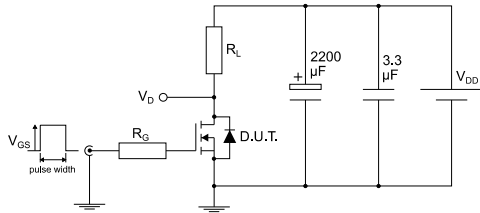
Figure 14: Maximum avalanche energy vs starting  $T_J$





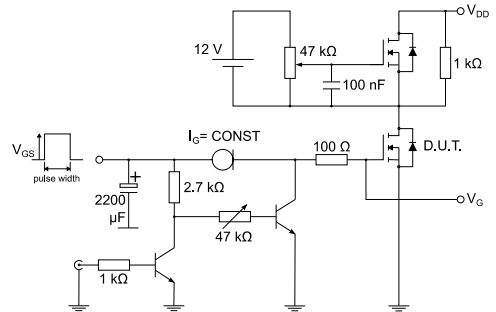
### 3 Test circuits

**Figure 15: Test circuit for resistive load switching times**



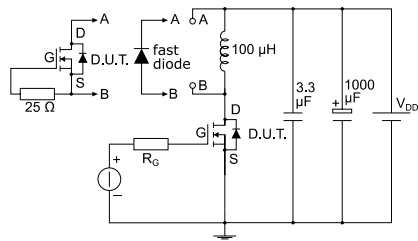
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**Figure 16: Test circuit for gate charge behavior**



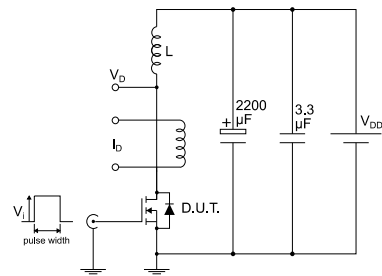
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**Figure 17: Test circuit for inductive load switching and diode recovery times**



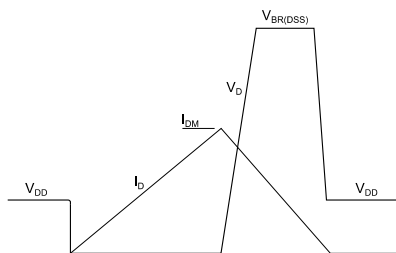
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**Figure 18: Unclamped inductive load test circuit**



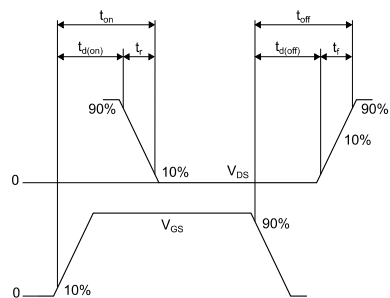
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**Figure 19: Unclamped inductive waveform**



AM01472v1

**Figure 20: Switching time waveform**



AM01473v1

## 4 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: [www.st.com](http://www.st.com). ECOPACK® is an ST trademark.

### 4.1 D<sup>2</sup>PAK (TO-263) type A package information

Figure 21: D<sup>2</sup>PAK (TO-263) type A package outline

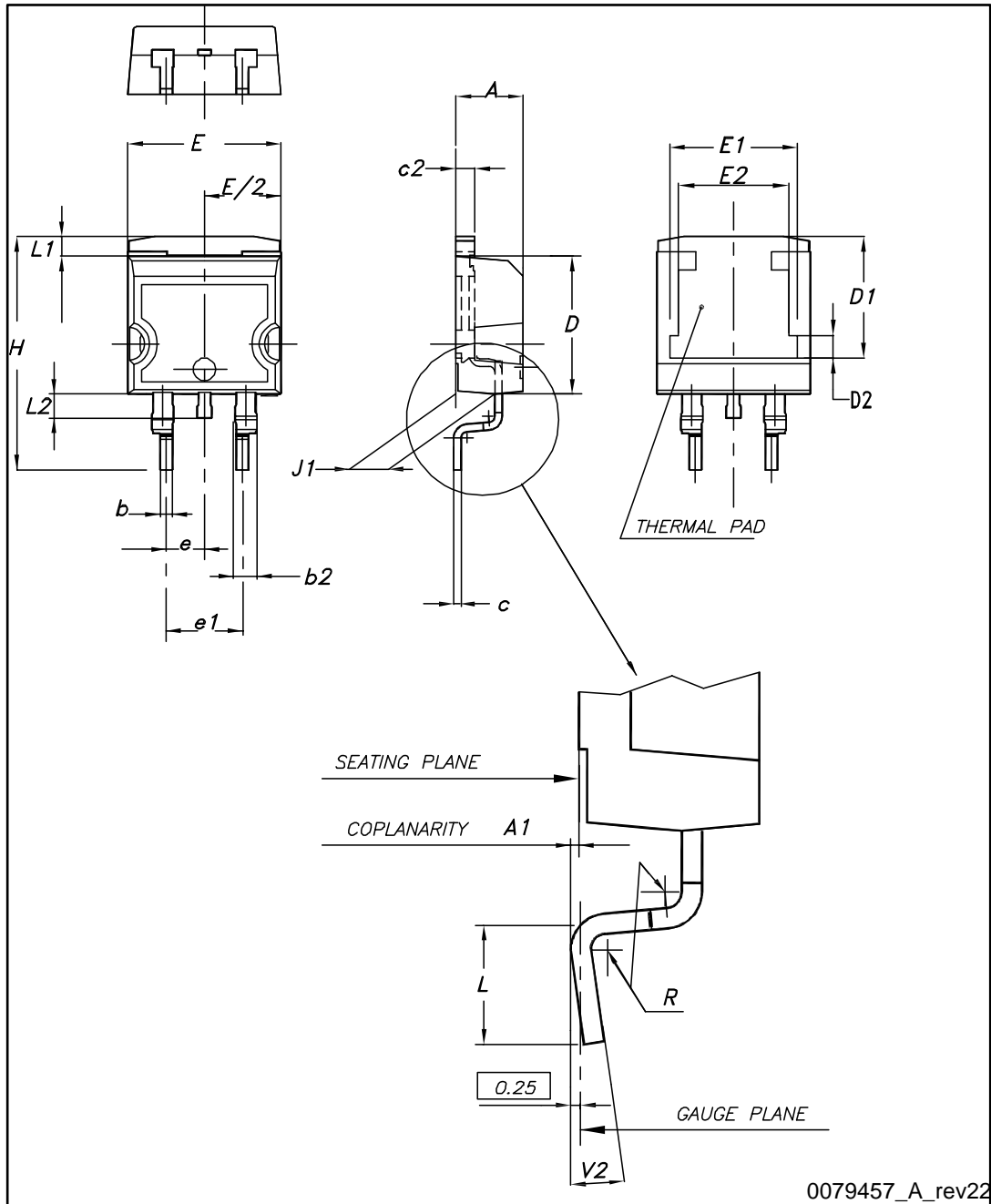
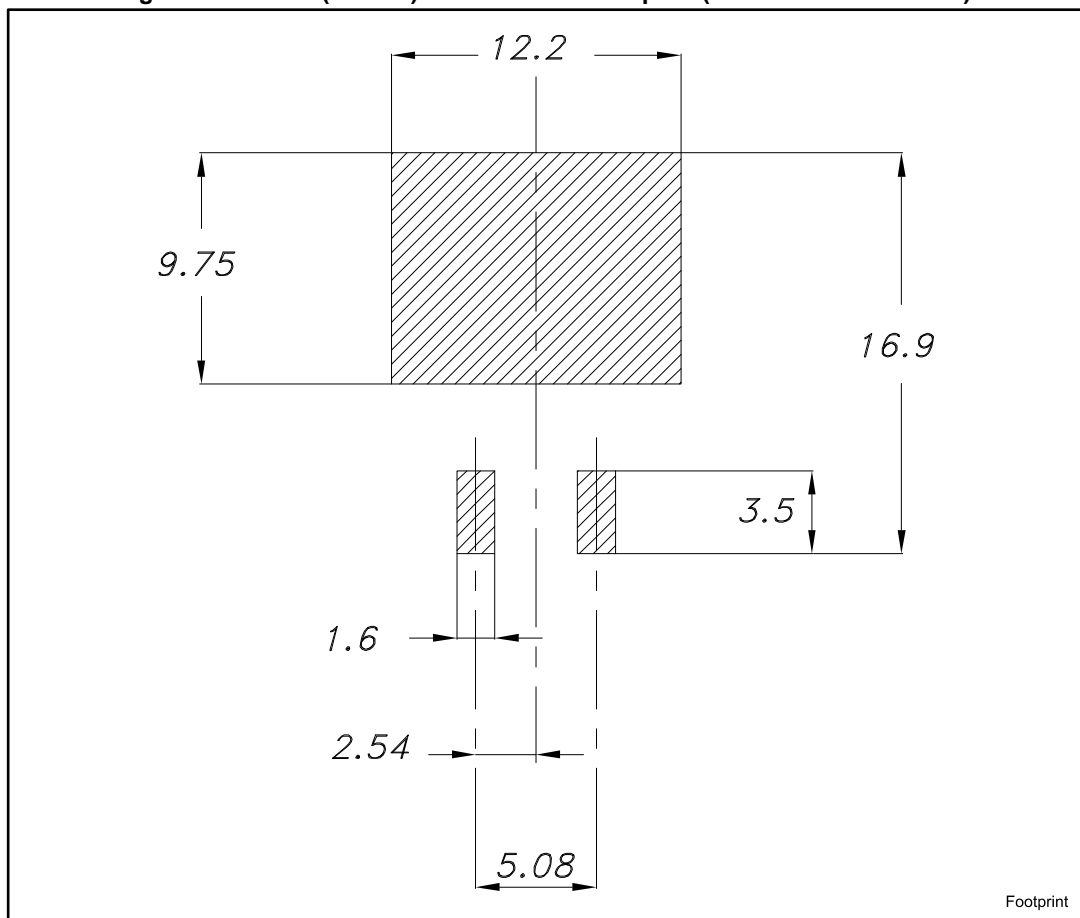


Table 10: D<sup>2</sup>PAK (TO-263) type A package mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
A1	0.03		0.23
b	0.70		0.93
b2	1.14		1.70
c	0.45		0.60
c2	1.23		1.36
D	8.95		9.35
D1	7.50	7.75	8.00
D2	1.10	1.30	1.50
E	10		10.40
E1	8.50	8.70	8.90
E2	6.85	7.05	7.25
e		2.54	
e1	4.88		5.28
H	15		15.85
J1	2.49		2.69
L	2.29		2.79
L1	1.27		1.40
L2	1.30		1.75
R		0.4	
V2	0°		8°

Figure 22: D<sup>2</sup>PAK (TO-263) recommended footprint (dimensions are in mm)



### 4.2 D<sup>2</sup>PAK (TO-263) packing information

Figure 23: Tape outline

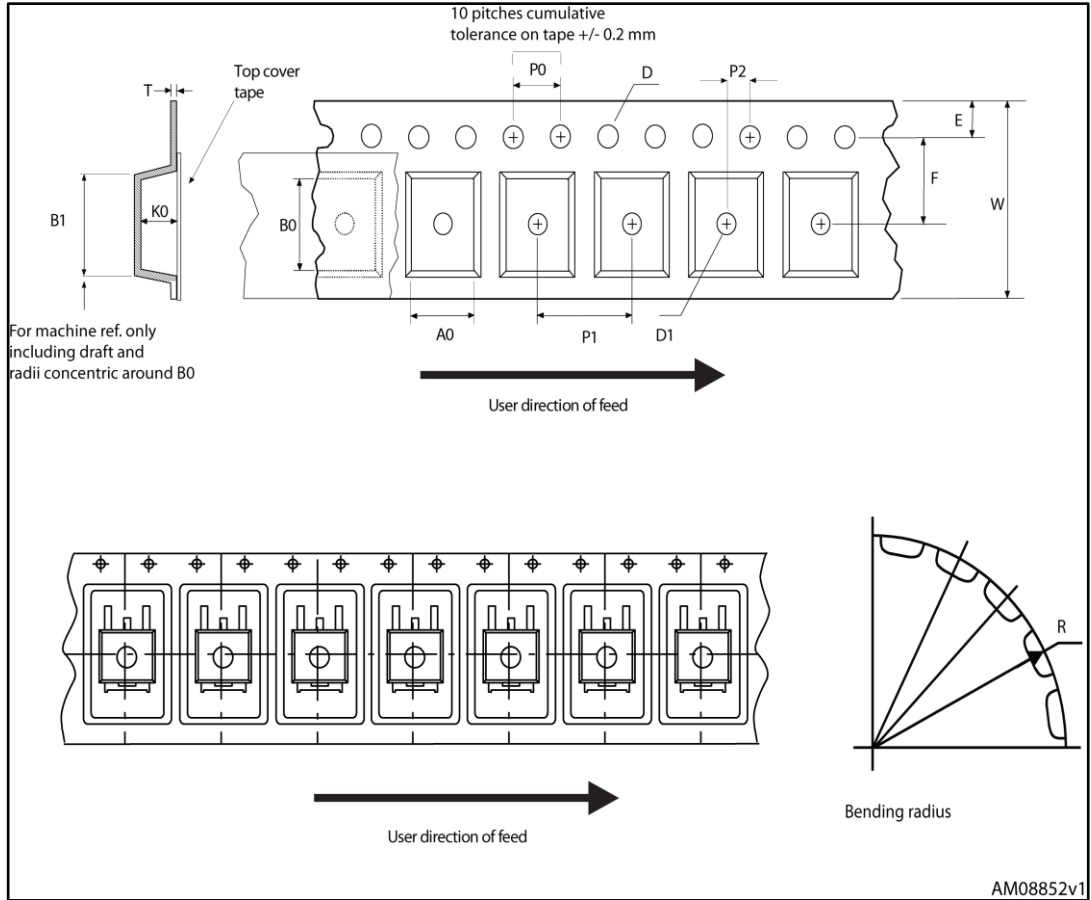


Figure 24: Reel outline

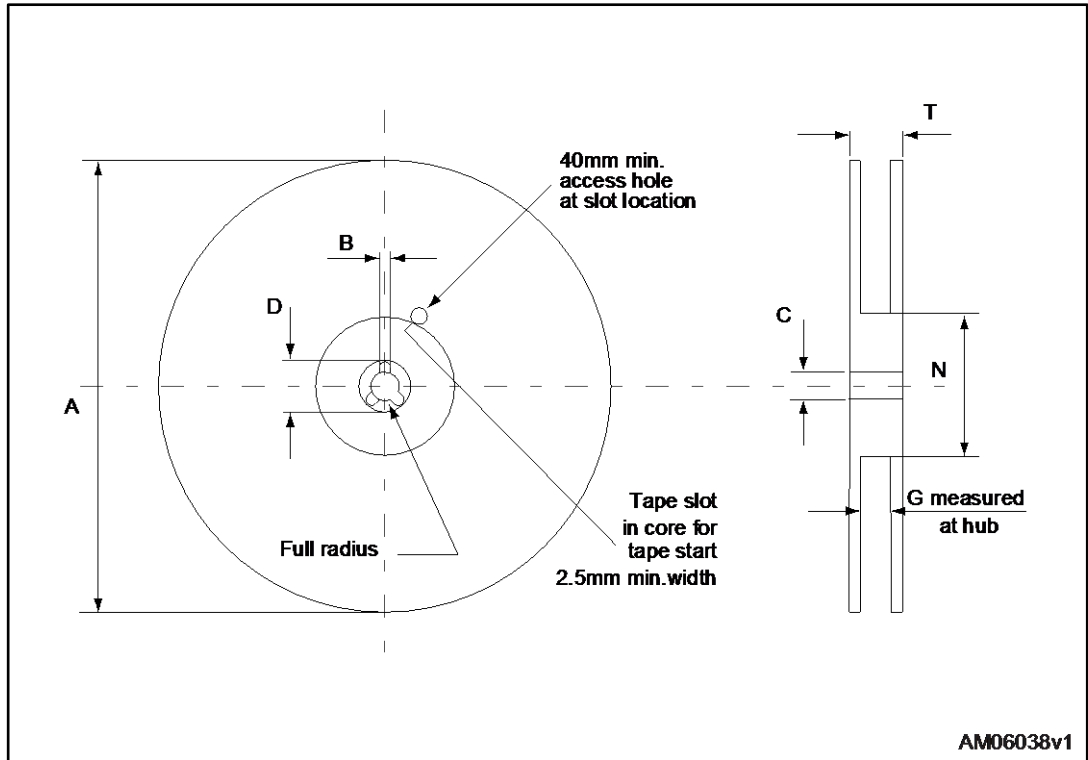


Table 11: D<sup>2</sup>PAK tape and reel mechanical data

Tape			Reel		
Dim.	mm		Dim.	mm	
	Min.	Max.		Min.	Max.
A0	10.5	10.7	A		330
B0	15.7	15.9	B	1.5	
D	1.5	1.6	C	12.8	13.2
D1	1.59	1.61	D	20.2	
E	1.65	1.85	G	24.4	26.4
F	11.4	11.6	N	100	
K0	4.8	5.0	T		30.4
P0	3.9	4.1			
P1	11.9	12.1	Base quantity		1000
P2	1.9	2.1	Bulk quantity		1000
R	50				
T	0.25	0.35			
W	23.7	24.3			

## 5 Revision history

Table 12: Document revision history

Date	Revision	Changes
18-Feb-2016	1	First release.

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